

POWER MANAGEMENT

PRELIMINARY

Description

The SC1104A/B is a versatile voltage-mode PWM controller designed for use in single ended DC/DC power supply applications. A simple, fixed frequency high efficiency buck regulator can be implemented using the SC1104A/B with a minimum of external components. Internal level shift and drive circuitry eliminates the need for an expensive P-channel, high-side switch. The small device footprint allows for compact circuit design.

SC1104A/B features include temperature compensated voltage reference, triangle wave oscillator, current limit comparator and an externally compensated error amplifier. Current limit is implemented by sensing the voltage drop across the top FET's $R_{DS(ON)}$.

The SC1104A/B operates at a fixed frequency of 300/600 kHz, providing an optimum compromise between efficiency, external component size, and cost. 600kHz switching frequency is typically reserved for the 5V operation only.

SC1104A/B has a thermal protection circuit, which is activated if the junction temperature exceeds 150°C.

Features

- ◆ +5V or +12V operation
- ◆ High efficiency (>90%)
- ◆ 1% Reference voltage accuracy
- ◆ Hiccup mode over current protection
- ◆ Robust output drive
- ◆ $R_{DS(ON)}$ Current sensing
- ◆ Industrial temperature range
- ◆ SO-8 package

Applications

- ◆ Termination supplies
- ◆ Low cost microprocessor supplies
- ◆ Peripheral card supplies
- ◆ Industrial power supplies
- ◆ High density DC/DC conversion

Typical Application Circuit

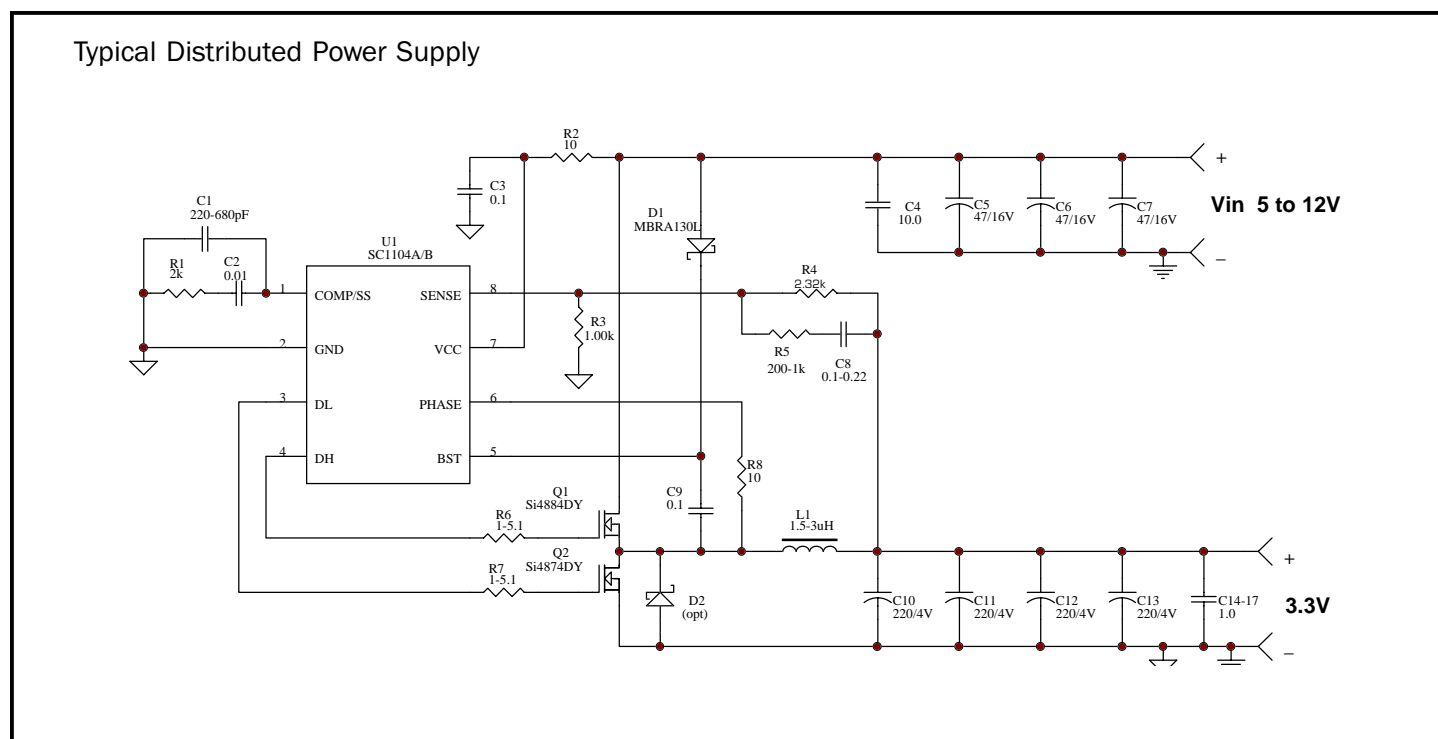


Figure 1

POWER MANAGEMENT
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Absolute Maximum Ratings

Parameter	Symbol	Maximum	Units
V_{CC} to GND		15	V
BST to PHASE		15	V
PHASE to GND		-1 to 15	V
DH to PHASE		15	V
DL to GND		15	V
COMP/SS to GND		7	V
SENSE to GND		7	V
Thermal Resistance Junction to Case	θ_{JC}	40	°C/W
Thermal Resistance Junction to Ambient	θ_{JA}	160	°C/W
Operating Temperature Range	T_A	-40 to +85	°C
Storage Temperature Range	T_{STG}	-65 to +150	°C
Lead Temperature (Soldering) 10 Sec.	T_{Lead}	300	°C

Electrical Characteristics

Unless specified: **A:** $V_{CC} = 12 \pm 0.6V$, $V_{BST} = 23 \pm 1V$, $V_{OUT} = 3.3V$, $T_A = 25^\circ C$. **B:** $V_{CC} = 5 \pm 0.25V$, $V_{BST} = 12 \pm 0.6V$, $V_{OUT} = 2.0V$, $T_A = 25^\circ C$

Parameter	Symbol	Conditions	Min	Typ	Max	Units
Power Supply						
Supply Voltage	V _{CC}	F _{SW} = 300kHz (nom.), (SC1104A)	4.2		12.6	V
	V _{CC}	F _{SW} = 600kHz (nom.), (SC1104B)	4.2		7	
Supply Current	I _{CC}	V _{COMP} ≤ 0.4V		11	14	mA
Error Amplifier						
E/A Transconductance	g _m			10		mS
Input Bias Current	I _{FB}			1	3	μA
Output Sink Current	I _{SIK}	V _{SENSE} ≥ 1.1V; V _{COMP} = 1.5V		0.7		mA
Source Current	I _{SC}	V _{SENSE} ≥ 0.9V; V _{COMP} = 1.5V		1.1		
Oscillator						
Switching Frequency	F _{OSC}	V _{CC} = 12V ± 0.6V	270	300	330	kHz
		V _{CC} = 5V ± 0.25V	540	600	660	
Ramp Peak Voltage	V _{P-K}	4.75V ≤ VCC ≤ 12.6V		2.0		V

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Parameter	Symbol	Conditions	Min	Typ	Max	Units
Ramp Valley Voltage	V _V	4.75V ≤ V _{CC} ≤ 12.6V		1.0		V
Maximum Duty Cycle	dc _{MAX}	V _{CC} = 12V (300kHz)		95		%
		V _{CC} = 5V (600kHz)		90		
MOSFET Drivers						
DH Sink/Source Current SC1104A	I _{DH}	d.c. < 2%, t _{PW} < 100μs V _{GS} = 4.5V (src)	0.7			A
DL Sink/Source Current SC1104A	I _{DL}	V _{GS} = 2.5V (snk)	0.7			
DH Sink/Source Current SC1104B	I _{DH}	d.c. < 2%, t _{PW} < 100μs V _{GS} = 4.5V (src)	0.5			A
DL Sink/Source Current SC1104B	I _{DL}	V _{GS} = 2.5V (snk)	0.5			
DH Rise/Fall Time	tr, tf	C _L = 3000pF, See Fig. 2		50		ns
DL Rise/Fall Time	tr, tf	C _L = 4000pF, See Fig. 2		50		
Dead Time	t _{dt}	See Fig. 2		80		ns
DH Minimum Off Time	t _{OFF}	4.75V ≤ Vcc ≤ 12.6V		160		
Reference Section						
Reference Voltage	V _{REF}	4.75V ≤ Vcc ≤ 12.6V	0.990	1.000	1.010	V
Reference Accuracy		-40 < T _A < 85°C	-1		1	%
Current Limit						
Trip Voltage	V _{trp}	4.75V < Vcc < 12.6V V _{trp} = Vcc - V _{PHASE}	180	200	220	mV
Soft-Start/Enable						
SS Source Current	I _{SRC}	V _{COMP} < 2.5V		1.5		μA
SS Sink Current	I _{SNK}	V _{COMP} > 0.5V		1.5		
Enable Input Threshold				1		V
Enable Input Current		V _{COMP} = 0.8V			2	mA
Under Voltage Lockout						
UVLO Threshold	V _{th}	-40< T _A < 85°C	3.9	4.15	4.5	V
Thermal Shutdown						
Over Temperature Trip Point	T _{OTP}			150		°C

Note: 1. This device is ESD sensitive. Use of standard ESD handling precautions is required.

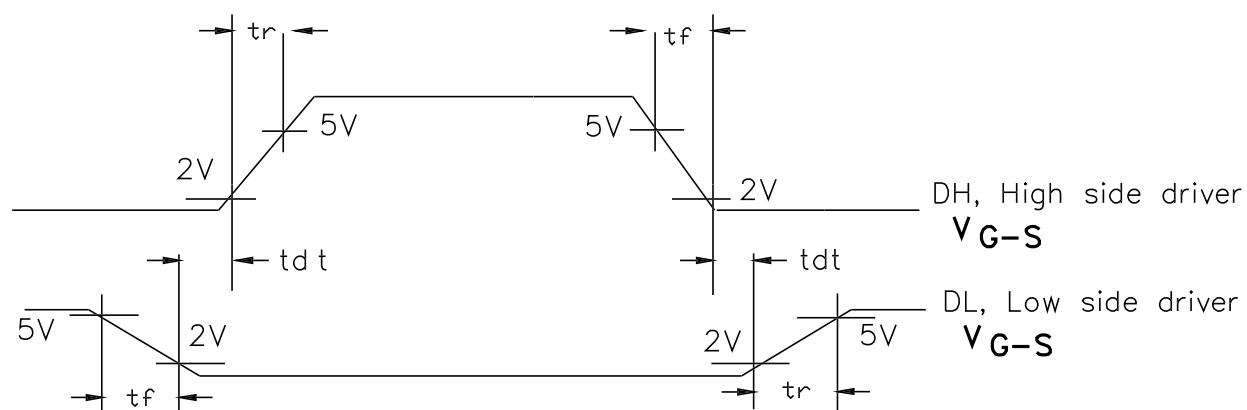


Figure 2

Block Diagram

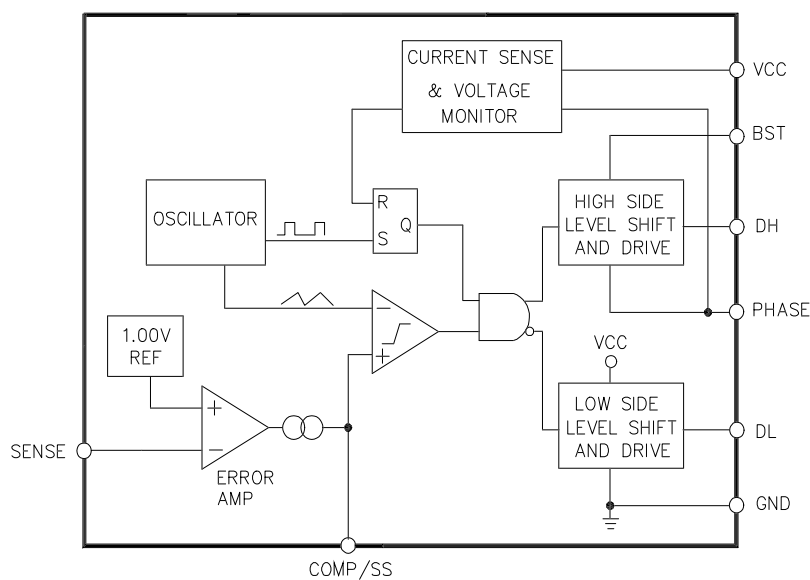
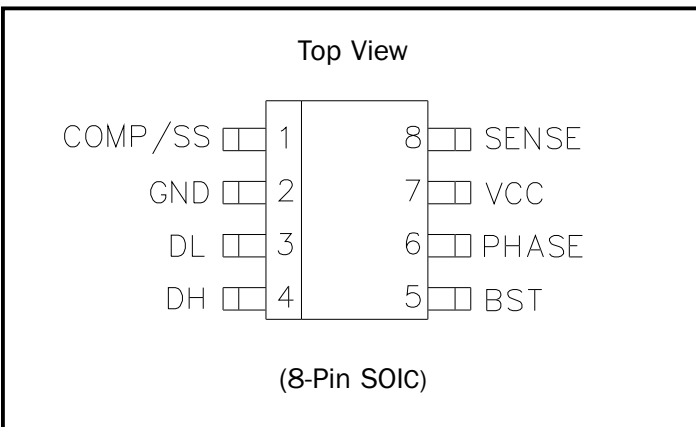


Figure 3

POWER MANAGEMENT
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Pin Configuration

Ordering Information

Device ⁽²⁾	Package	Temp Range (T _j)
SC1104XISTR ⁽¹⁾	SOIC-8	-40° to 125°C

Note:

(1) In place of "X": A = 300kHz; B = 600kHz.

(2) Only available in tape and reel packaging. A reel contains 2500 devices.

Pin Descriptions

Pin #	Pin Name	Pin Function
1	COMP/SS	Error amplifier output. Compensation, soft start/enable.
2	GND	Ground.
3	DL	Low side driver output
4	DH	High side driver output
5	BST	Bootstrap, high side driver.
6	PHASE	Input from the phase node between the MOSFETs.
7	VCC	Chip bias supply voltage.
8	SENSE	Output voltage sense input.

POWER MANAGEMENT
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Theory of Operation
Synchronous Buck Converter

The output voltage of the synchronous converter is set and controlled by the output of the error amplifier. The inverting input of the error amplifier receives its voltage from the SENSE pin.

The non-inverting input of the error amplifier is connected to an internal 1V reference.

The error amplifier output is connected to the COMPensation pin. The error amplifier generates a current proportional to $(V_{\text{sense}} - 1V)$, which is the COMP pin output current (Transconductance $\sim 10\text{mS}$). The voltage on the COMP pin is the integral of the error amplifier current. The COMP voltage is the non-inverting input to the PWM comparator and controls the duty cycle of the MOSFET drivers. The size of capacitor C_{comp} controls the stability and transient response of the regulator. The larger the capacitor, the slower the COMP voltage changes, and the slower the duty cycle changes.

The inverting input voltage of the PWM comparator is the triangular output of the oscillator.

When the oscillator output voltage drops below the COMP voltage, the comparator output goes high. This pulls DL low, turning off the low-side FET. After a short delay ("dead time"), DH is pulled high, turning on the high-side FET. When the oscillator voltage rises back above the error amplifier output voltage, the comparator output goes low. This pulls DH low, turning off the high-side FET, and after a dead time delay, DL is pulled high, turning on the low-side FET. The dead time delay is determined by a monostable on the chip.

The triangle wave minimum is about 1V, and the maximum is about 2V. Thus, if $V_{\text{comp}} = 0.9V$, high side duty cycle is the minimum ($\sim 0\%$), but if V_{comp} is 2.0V, duty cycle is at maximum ($\sim 80\%$). The internal oscillator uses an on-chip capacitor and trimmed precision current sources to set the oscillation frequency to 300/600kHz.

Figure 1 shows a 3.3V output converter. If the $V_{\text{out}} < 3.3V$, then the SENSE voltage $< 1V$. In this case the error amplifier will be sourcing current into the COMP pin so that COMP voltage and duty cycle will gradually increase. If $V_{\text{out}} > 3.3V$, the error amplifier will sink current and reduce the COMP voltage, so that duty cycle will decrease.

The circuit will be in steady state when $V_{\text{out}} = 3.3V$, $V_{\text{sense}} = 1V$, $I_{\text{comp}} = 0$. The COMP voltage and duty cycle depend on V_{in} .

Under Voltage Lockout

The under voltage lockout circuit of the SC1104A/B assures that both high-side and low-side MOSFET driver outputs remain in the off state whenever the supply voltage drops below set parameters. Lockout occurs if V_{cc} falls below 4.2V typ.

 $R_{\text{DS(ON)}}$ Current Limiting

In case of a short circuit or overload, the high-side (HS) FET will conduct large currents. To prevent damage, in this situation, large currents will generate a fault condition and begin a soft start cycle.

While the HS driver is on, the phase voltage is compared to the V_{cc} pin voltage. If the phase voltage is 200mV lower than V_{cc} , a fault is latched and the soft start cycle begins.

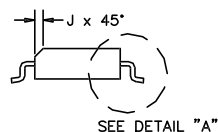
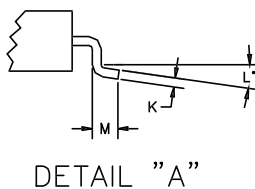
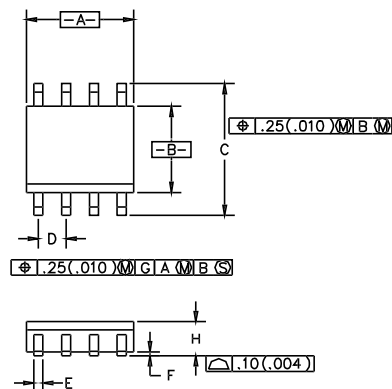
The voltages are compared during the middle of the HS pulse, to prevent transients from affecting the accuracy.

Soft Start

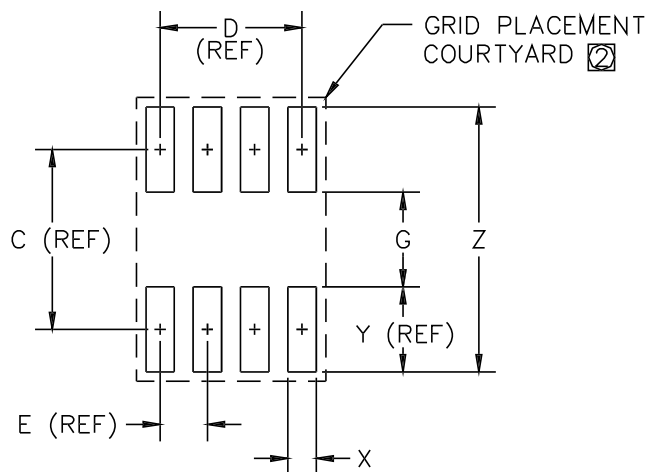
The soft start (or hiccup) circuitry is activated when a fault occurs. Faults occur for three reasons:

- 1) Under voltage ($V_{\text{cc}} < 4.2V$)
- 2) Over temperature (die temperature $> 150^{\circ}\text{C}$)
- 3) Over current in high side FET.

All faults are handled the same way. Both DH and DL are forced low. The error amplifier is turned off, but a $2\mu\text{A}$ current flows into the comp pin (soft start current). The sink current reduces the Comp voltage down to 0.6V over a period of a few milliseconds. When $V_{\text{comp}} \sim 0.6V$, the fault is cleared and the DL goes high. Also, the soft start current changes polarity and begins to increase the voltage on the Comp capacitor. The DH remains low, because V_{comp} is less than the lowest excursion of the oscillator ramp (1.0V). After a few ms, the V_{comp} increases to about 1.0V and the DH will start to switch. The duty cycle will gradually increase, and V_{sns} will increase. When $V_{\text{sns}} \sim 1.00V$, the error amplifier turns on again. The circuit has now reached its operating point. If a fault occurs during the soft start, the cycle will begin again (drivers low, V_{comp} decreasing down to 0.6V).

Outline Drawing - S0-8


DIM ^N	INCHES		MM		NOTE
	MIN	MAX	MIN	MAX	
A	.188	.197	4.80	5.00	
B	.149	.158	3.80	4.00	
C	.228	.244	5.80	6.20	
D	.050	BSC	1.27	BSC	
E	.013	.020	0.33	0.51	
F	.004	.010	0.10	0.25	
H	.053	.069	1.35	1.75	
J	.011	.019	0.28	0.48	
K	.007	.010	.19	.25	
L	0°	8°	0°	8°	
M	.016	.050	0.40	1.27	

Land Pattern - S0-8


DIM ^N	INCHES		MM		NOTE
	MIN	MAX	MIN	MAX	
C	—	.19	—	5.00	—
D	—	.15	—	3.81	—
E	—	.05	—	1.27	—
G	.10	.11	2.60	2.80	—
X	.02	.03	.60	.80	—
Y	—	.09	—	2.40	—
Z	—	.29	7.20	7.40	—

② GRID PLACEMENT COURTYARD IS 12x16 ELEMENTS (6 mm X 8mm) IN ACCORDANCE WITH THE INTERNATIONAL GRID DETAILED IN IEC PUBLICATION 97.

① CONTROLLING DIMENSION: MILLIMETERS

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